Claim 24, line 28, delete "any of claims 19 to 23" and insert -- Claim 19 --.

PLEASE ADD THE FOLLOWING CLAIMS:

25. Process according to Claim 3, characterized in that doping agents are associated with the one or more gas species.

26. Process according to Claim 6, characterized in that said implantation is made via the substrate surface, the region lying between the substrate surface and the layer of microcavities providing said thin layer.

27. Process according to Claim 6, characterized in that said implantation is made via the substrate surface, this surface carrying a first thin layer, the region lying between the substrate and the layer of microcavities providing a second thin layer.

28. Process according to Claim 11, characterized in that implantation by bombardment is made via a sacrificial layer carried by the first thin layer, said sacrificial layer then being removed.

29. Compliant substrate according to Claim 14, characterized in that said joining zone also comprises at least one intermediate layer (22; 32, 33) between the thin layer (23; 34) and the carrier (21; 31).

30. Compliant substrate according to Claim 17, characterized in that the joining means comprise a layer of microcavities and a bonding interface arranged either above or below the layer of microcavities.

A1 Cont.

31. Compliant substrate (5, 20, 30) according to Claim 18, characterized in that said thin layer (4, 13, 23, 34) is in a first crystalline material and is intended to be used as hetero-epitaxial growth seed for a second crystalline material forming said structure.

32. Compliant substrate according to Claim 21, characterized in that said foreign element is a doping agent of the thin layer.

33. Compliant substrate (5, 20, 30) according to Claim 22, characterized in that said first crystalline material is a semiconductor.

34. Application of the compliant substrate (5, 20, 30) according to Claim 23, to the hetero-epitaxial growth of a crystalline material chosen from among GaN, SiGe, AlN, InN and SiC.